

CLAIMS:

What is claimed is:

- SUB
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1. A method for the fabrication of a Schottky barrier diode on a SiC wafer, comprising the steps of:
 - (a) placing a mask having a window on a surface of the SiC wafer;
 - (b) depositing conductive material on the mask and exposed portions of the wafer surface;
 - (c) stripping off the mask so as to leave the conductive material deposited upon portions of the wafer surface; and
 - (d) implanting an edge termination layer to the wafer beneath the surface thereof but not beneath the conductive material.
 2. The method for the fabrication of a Schottky barrier diode on a SiC wafer as described in claim 1, further comprising the steps of:
 - (a) before placing the mask, forming an insulating layer on the surface of the wafer;
 - (b) applying the mask to the insulating layer; and
 - (c) etching away a portion of the insulating layer that is within the window to expose the SiC wafer therebeneath before depositing the conductive material.

- Illegible text (likely a header or title) consisting of approximately 15 lines of characters.

SILICON CARBIDE SCHOTTKY BARRIER
DIODE AND METHOD OF MAKING

15. The Schottky barrier diode as described in claim 9, wherein the
conductive layer is formed of a metal.
16. The Schottky barrier diode as described in claim 15, wherein the
metal is titanium.
17. The Schottky barrier diode as described in claim 9, wherein the
conductive layer has a thickness greater than a thickness of the
insulating layer.

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